# 8-Bit Dual-Supply Inverting **Level Translator**

The NLSV8T240 is a 8-bit configurable dual-supply voltage level translator. The input A<sub>n</sub> and output B<sub>n</sub> ports are designed to track two different power supply rails, V<sub>CCA</sub> and V<sub>CCB</sub> respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input  $A_n$  to the output  $B_n$  port.

#### **Features**

- Wide V<sub>CCA</sub> and V<sub>CCB</sub> Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V<sub>CCA</sub> and V<sub>CCB</sub> Sequencing
- Outputs at 3-State until Active V<sub>CC</sub> is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V<sub>CCB</sub> at GND
- Ultra-Small Packaging: 4.0 mm x 2.0 mm UDFN20
- This is a Pb-Free Device

### **Typical Applications**

• Mobile Phones, PDAs, Other Portable Devices

#### **Important Information**

• ESD Protection for All Pins: HBM (Human Body Model) > 7000 V

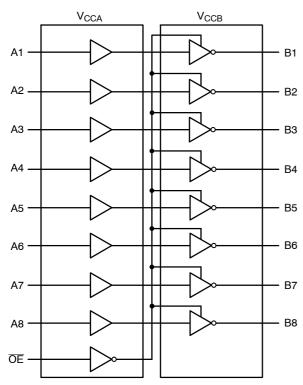


Figure 1. Logic Diagram



### ON Semiconductor®

http://onsemi.com



#### **MARKING DIAGRAM**



UDFN20 **MU SUFFIX CASE 517AK** 

LB = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

#### **PIN ASSIGNMENT**

$V_{CCA}$	1	)	20	$V_{CCB}$
A1	_2		19	B1
A2	3		18	B2
АЗ	_4 ]			ВЗ
A4	_5 ]			B4
<b>A</b> 5	_6			B5
A6	7		14	B6
A7	_8		13	В7
A8	_9 <u></u>		12	В8
GND	10 ]			ŌĒ
		· · · ·		

(Top View)

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NLSV8T240MUTAG	UDFN20 (Pb-Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

### **PIN ASSIGNMENT**

PIN	FUNCTION
V <sub>CCA</sub>	Input Port DC Power Supply
V <sub>CCB</sub>	Output Port DC Power Supply
GND	Ground
A <sub>n</sub>	Input Port
B <sub>n</sub>	Output Port
ŌĒ	Output Enable

### **TRUTH TABLE**

In	Inputs			
ŌĒ	A <sub>n</sub>	B <sub>n</sub>		
L	L	Н		
L	Н	L		
Н	Х	3-State		

### **MAXIMUM RATINGS**

Symbol	Rating		Value	Condition	Unit
V <sub>CCA</sub> , V <sub>CCB</sub>	DC Supply Voltage		-0.5 to +5.5		V
VI	DC Input Voltage	An	-0.5 to +5.5		V
V <sub>C</sub>	Control Input	ŌΕ	-0.5 to +5.5		V
V <sub>O</sub>	DC Output Voltage (Power Down)	B <sub>n</sub>	-0.5 to +5.5	$V_{CCA} = V_{CCB} = 0$	V
	(Active Mode)	B <sub>n</sub>	-0.5 to +5.5		V
	(Tri-State Mode)	B <sub>n</sub>	-0.5 to +5.5		V
I <sub>IK</sub>	DC Input Diode Current		-20	V <sub>I</sub> < GND	mA
lok	DC Output Diode Current		-50	V <sub>O</sub> < GND	mA
I <sub>O</sub>	DC Output Source/Sink Current		±50		mA
I <sub>CCA</sub> , I <sub>CCB</sub>	DC Supply Current Per Supply Pin		±100		mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±100		mA
T <sub>STG</sub>	Storage Temperature		-65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CCA</sub> , V <sub>CCB</sub>	Positive DC Supply Voltage		0.9	4.5	V
V <sub>I</sub>	Bus Input Voltage		GND	4.5	V
V <sub>C</sub>	Control Input	ŌĒ	GND	4.5	V
V <sub>IO</sub>	Bus Output Voltage (Power Down Mode)	B <sub>n</sub>	GND	4.5	V
	(Active Mode)	B <sub>n</sub>	GND	V <sub>CCB</sub>	V
	(Tri-State Mode)	B <sub>n</sub>	GND	4.5	V
T <sub>A</sub>	Operating Temperature Range		-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate V <sub>I</sub> , from 30% to 70% of V <sub>CC</sub> ; V <sub>CC</sub> = 3.3 V $\pm$ 0.3 V		0	10	nS

### DC ELECTRICAL CHARACTERISTICS

					-40°C to	5 +85°C	
Symbol	Parameter	Test Conditions	V <sub>CCA</sub> (V)	V <sub>CCB</sub> (V)	Min	Max	Uni
V <sub>IH</sub>	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.2	-	V
	(An, $\overline{OE}$ )		2.7 – 3.6		2.0	-	
			2.3 – 2.7		1.6	-	
			1.4 – 2.3		0.65 * V <sub>CCA</sub>	-	
			0.9 – 1.4		0.9 * V <sub>CCA</sub>	-	
V <sub>IL</sub>	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	-	0.8	V
	(An, $\overline{OE}$ )		2.7 – 3.6	1	-	0.8	
			2.3 – 2.7	1	-	0.7	
			1.4 – 2.3	1	-	0.35 * V <sub>CCA</sub>	
			0.9 – 1.4	1	-	0.1 * V <sub>CCA</sub>	
V <sub>OH</sub>	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IL}$	0.9 – 4.5	0.9 – 4.5	V <sub>CCB</sub> - 0.2	-	V
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IL}$	0.9	0.9	0.75 * V <sub>CCB</sub>	-	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IL}$	1.4	1.4	1.05	-	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	1.25	-	
			2.3	2.3	2.0	-	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IL}$	2.3	2.3	1.8	-	
			2.7	2.7	2.2	-	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IL}$	2.3	2.3	1.7	-	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IL}$	3.0	3.0	2.2	_	
V <sub>OL</sub>	Output LOW Voltage	$I_{OL} = 100 \mu A; V_I = V_{IH}$	0.9 – 4.5	0.9 – 4.5	-	0.2	V
		I <sub>OL</sub> = 0.5 mA; V <sub>I</sub> = V <sub>IH</sub>	1.1	1.1	-	0.3	
		$I_{OL} = 2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	-	0.35	
		I <sub>OL</sub> = 6 mA; V <sub>I</sub> = V <sub>IH</sub>	1.65	1.65	-	0.3	
		I <sub>OL</sub> = 12 mA; V <sub>I</sub> = V <sub>IH</sub>	2.3	2.3	-	0.4	
			2.7	2.7	-	0.4	
		$I_{OL}$ = 18 mA; $V_I$ = $V_{IH}$	2.3	2.3	-	0.6	
			3.0	3.0	-	0.4	
		$I_{OL}$ = 24 mA; $V_I$ = $V_{IH}$	3.0	3.0	-	0.55	
lį	Input Leakage Current	V <sub>I</sub> = V <sub>CCA</sub> or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μA
I <sub>OFF</sub>	Power-Off Leakage Current	<u>OE</u> = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μΔ
I <sub>CCA</sub>	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$ , $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μA
I <sub>CCB</sub>	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$ , $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μÆ
CA + ICCB	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$ , $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	4.0	μA
$\Delta I_{CCA}$	Increase in $I_{CC}$ per Input Voltage, Other Inputs at $V_{CCA}$ or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μA
$\Delta I_{CCB}$	Increase in $I_{CC}$ per Input Voltage, Other Inputs at $V_{CCA}$ or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	_	10 5.0	μA
l <sub>OZ</sub>	I/O Tri-State Output Leakage	T <sub>A</sub> = 25°C, <del>OE</del> = 0 V	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μA

TOTAL STATIC POWER CONSUMPTION (I<sub>CCA</sub> + I<sub>CCB</sub>)

					-40°C to	o +85°C					
					V <sub>CCI</sub>	<sub>B</sub> (V)					
	4	.5	3.	.3	2.	.8	1.	8	0.	.9	
V <sub>CCA</sub> (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

 $NOTE: Connect ground before applying supply voltage \ V_{CCB}. This device is designed with the feature that the power-up sequence$ of  $V_{CCA}$  and  $V_{CCB}$  will not damage the IC.

### **AC ELECTRICAL CHARACTERISTICS**

							-40°C t	o +85°C					
							V <sub>CC</sub>	<sub>B</sub> (V)					
			4	.5	3	.3	2	.8	1	.8	1.	2	
Symbol	Parameter	V <sub>CCA</sub> (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation	4.5		1.6		1.8		2.0		2.1		2.3	nS
t <sub>PHL</sub> (Note 1)	Delay,	3.3		1.7		1.9		2.1		2.3		2.6	
(Note 1)	A <sub>n</sub> to B <sub>n</sub>	2.8		1.9		2.1		2.3		2.5		2.8	
		1.8		2.1		2.4		2.5		2.7		3.0	
		1.2		2.4		2.7		2.8		3.0		3.3	
t <sub>PZH</sub> ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t <sub>PZL</sub> (Note 1)	Enable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B <sub>n</sub>	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t <sub>PHZ</sub> ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t <sub>PLZ</sub>	Disable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B <sub>n</sub>	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t <sub>OSHL</sub> ,	LH Output	4.5		0.15		0.15		0.15		0.15		0.15	nS
t <sub>OSLH</sub>		3.3		0.15		0.15		0.15		0.15		0.15	
(Note 1)		2.5		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

<sup>1.</sup> Propagation delays defined per Figure 2.

#### **CAPACITANCE**

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C <sub>IN</sub>	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C <sub>I/O</sub>	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C <sub>PD</sub>	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	20	pF

Typical values are at T<sub>A</sub> = +25°C.
 C<sub>PD</sub> is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I<sub>CC(operating)</sub> ≅ C<sub>PD</sub> x V<sub>CC</sub> x f<sub>IN</sub> x N<sub>SW</sub> where I<sub>CC</sub> = I<sub>CCA</sub> + I<sub>CCB</sub> and N<sub>SW</sub> = total number of outputs switching.

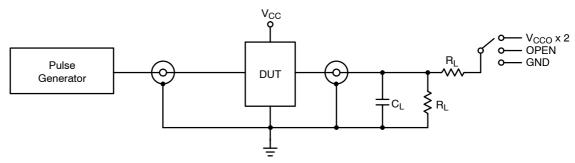


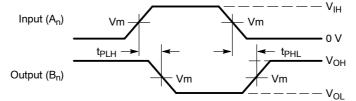
Figure 2. AC (Propagation Delay) Test Circuit

Test	Switch
t <sub>PLH</sub> , t <sub>PHL</sub>	OPEN
t <sub>PLZ</sub> , t <sub>PZL</sub>	V <sub>CCO</sub> x 2
t <sub>PHZ</sub> , t <sub>PZH</sub>	GND

 $C_L$  = 15 pF or equivalent (includes probe and jig capacitance)

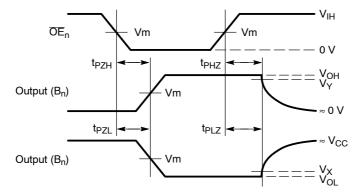
 $R_L = 2 k\Omega$  or equivalent

 $Z_{OUT}$  of pulse generator = 50  $\Omega$ 



### Waveform 1 - Propagation Delays

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$ 



#### Waveform 2 - Output Enable and Disable Times

 $t_{R}$  =  $t_{F}$  = 2.0 ns, 10% to 90%; f = 1 MHz;  $t_{W}$  = 500 ns

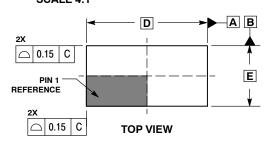
Figure 3. AC (Propagation Delay) Test Circuit Waveforms

	V <sub>CC</sub>									
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V					
V <sub>mA</sub>	V <sub>CCA</sub> /2									
V <sub>mB</sub>	V <sub>CCB</sub> /2									
V <sub>X</sub>	V <sub>OL</sub> x 0.1									
$V_{Y}$	V <sub>OH</sub> x 0.9									



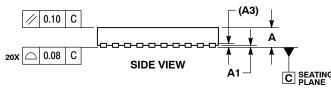
UDFN20 4x2, 0.4P CASE 517AK-01 **ISSUE O** 

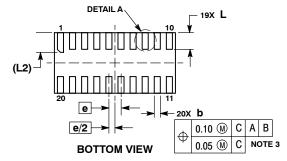
**DATE 14 NOV 2006** 



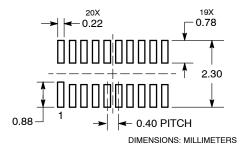


NOTE 5





#### MOUNTING FOOTPRINT **SOLDERMASK DEFINED**



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM TERMINAL TIP.
- MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS.
- 5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

	MILLIN	MILLIMETERS		
DIN	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.13	0.13 REF		
b	0.15	0.25		
D	4.00	4.00 BSC		
E	2.00 BSC			
е	0.40	0.40 BSC		
L	0.50	0.60		
L1	0.00	0.03		
L2	0.60	0.70		

### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON23419D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	UDFN20 4 X 2, 0.4P		PAGE 1 OF 1

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative